

FS5ASJ-2

High-Speed Switching Use Nch Power MOS FET

REJ03G1405-0300 Rev.3.00 Nov 21, 2006

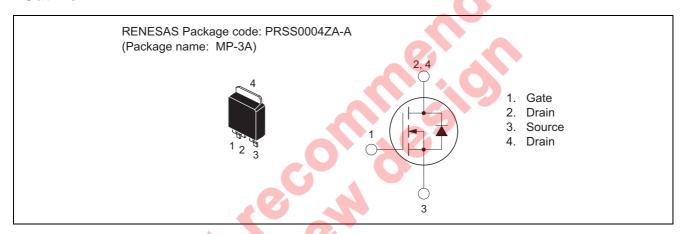
Features

 $\begin{tabular}{ll} \bullet & Drive \ voltage: 4 \ V \\ \bullet & V_{DSS}: 100 \ V \\ \bullet & r_{DS(ON) \, (max)}: 0.4 \ \Omega \\ \end{tabular}$

• I_D: 5 A

• Integrated Fast Recovery Diode (TYP.): 80 ns

Outline



Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

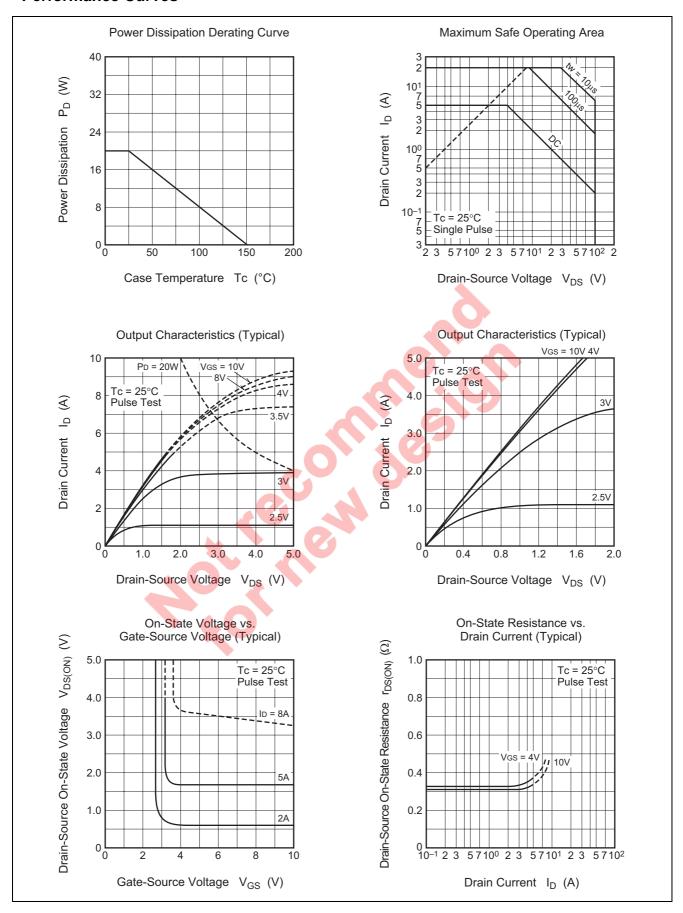
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	100	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	$V_{DS} = 0 V$
Drain current	I _D	5	А	
Drain current (Pulsed)	I _{DM}	20	А	
Avalanche drain current (Pulsed)	I _{DA}	5	А	L = 100 μH
Source current	Is	5	А	
Source current (Pulsed)	I _{SM}	20	А	
Maximum power dissipation	P_D	20	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	<u> </u>	0.32	g	Typical value

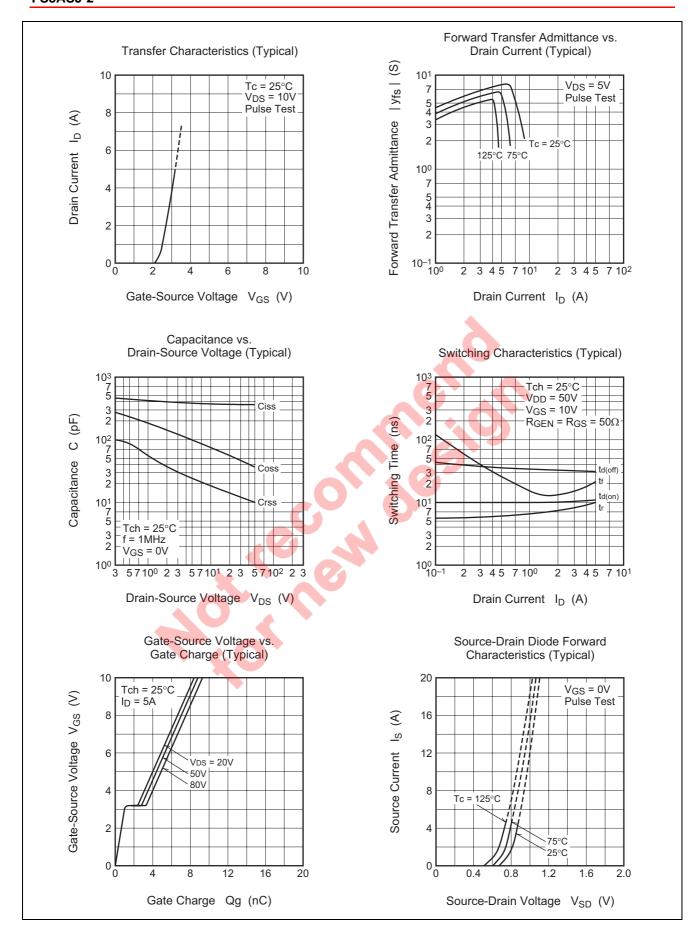
Electrical Characteristics

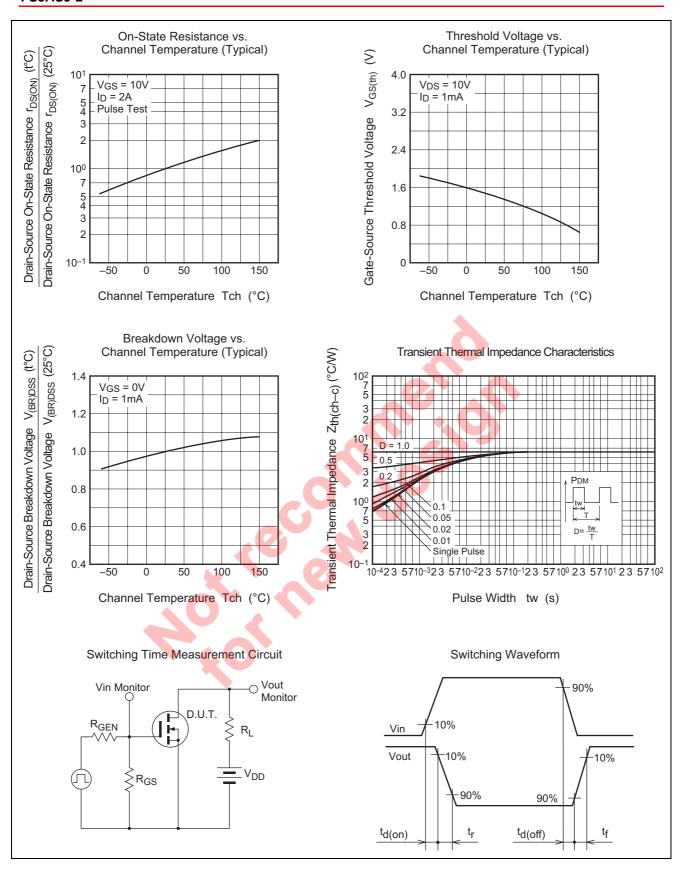
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions		
Drain-source breakdown voltage	V _{(BR)DSS}	100	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$		
Gate-source leakage current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		
Drain-source leakage current	I _{DSS}	_	_	0.1	mA	V _{DS} = 100 V, V _{GS} = 0 V		
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$		
Drain-source on-state resistance	r _{DS(ON)}	_	0.31	0.40	Ω	$I_D = 2 A, V_{GS} = 10 V$		
Drain-source on-state resistance	r _{DS(ON)}	_	0.34	0.46	Ω	$I_D = 2 A, V_{GS} = 4 V$		
Drain-source on-state voltage	V _{DS(ON)}	_	0.62	0.8	V	$I_D = 2 A, V_{GS} = 10 V$		
Forward transfer admittance	y _{fs}	_	6	_	S	$I_D = 2 A, V_{DS} = 5 V$		
Input capacitance	Ciss	_	360	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		
Output capacitance	Coss	_	75	_	pF	f = 1MHz		
Reverse transfer capacitance	Crss	_	20	_	pF			
Turn-on delay time	t _{d(on)}	_	10	_	ns	$V_{DD} = 50 \text{ V}, I_D = 2 \text{ A},$		
Rise time	t _r	_	7	_	ns	$V_{GS} = 10 \text{ V},$		
Turn-off delay time	t _{d(off)}	_	35	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$		
Fall time	t _f	_	15	_ (ns			
Source-drain voltage	V_{SD}	_	1.0	1.5	V	I _S = 2 A, V _{GS} = 0 V		
Thermal resistance	R _{th(ch-c)}	_	_	6.25	°C/W	Channel to case		
Reverse recovery time	t _{rr}	_	80	(4)	ns	$I_S = 5 \text{ A}, d_{is}/dt = -100 \text{ A}/\mu \text{s}$		
Reverse recovery time $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$								

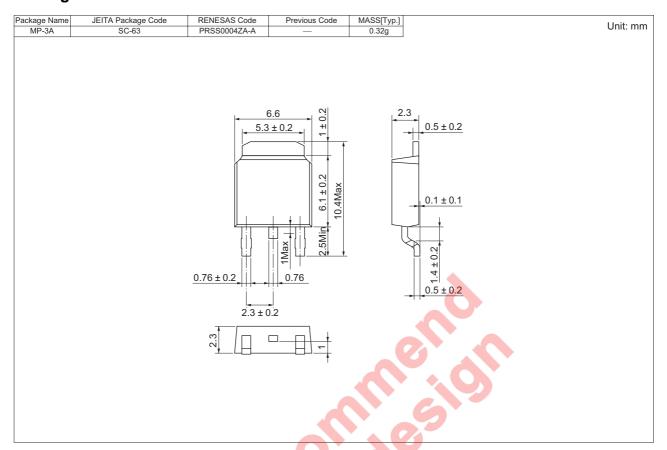
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Qı	uantity	Standard order code	Standard order code example
Surface-mounted type	Taping		3000	Type name – T +Direction (1 or 2) +3	FS5ASJ-2-T13
Surface-mounted type	Plastic Magazine (Tube)		75	Type name	FS5ASJ-2

Note: Please confirm the specification about the shipping in detail.

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